



TO-220

TO-251
(IPAK)TO-252
(DPAK)**Pin Definition:**

1. Gate
2. Drain
3. Source

TSM2N60

600V N-Channel Power MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
600	4.4 @ $V_{GS}=10V$	1

General Description

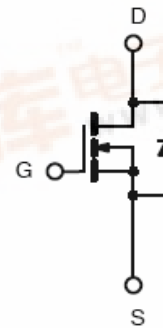
The TSM2N60 is used an advanced termination scheme to provide enhanced voltage-blocking capability without degrading performance over time. In addition, this advanced MOSFET is designed to withstand high energy in avalanche and commutation modes. The new energy efficient design also offers a drain- to-source diode with a fast recovery time. Designed for high voltage, high speed switching applications in power supplies, converters and PWM motor controls, these devices are particularly well suited for bridge circuits where diode speed and commutating safe operating areas are critical and offer additional and safety margin against unexpected voltage transients.

Features

- Robust high voltage termination
- Avalanche energy specified
- Diode is characterized for use in bridge circuits
- Source to Drain diode recovery time comparable to a discrete fast recovery diode.

Ordering Information

Part No.	Package	Packing
TSM2N60CP RO	TO-252	2.5Kpcs/ 13" Reel
TSM2N60CH C5	TO-251	80pcs / Tube
TSM2N60CZ C0	TO-220	50pcs / Tube

Block Diagram

N-Channel MOSFET

Absolute Maximum Rating ($T_a = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	600	V
Gate-Source Voltage	V_{GS}	± 30	V
Continuous Drain Current	I_D	2	A
Pulsed Drain Current	I_{DM}	9	A
Continuous Source Current (Diode Conduction) ^{a,b}	I_S	1	A
Single Pulse Drain to Source Avalanche Energy ($V_{DD} = 100V$, $V_{GS}=10V$, $I_{AS}=2A$, $L=10mH$, $R_G=25\Omega$)	EAS	20	mJ
Maximum Power Dissipation @ $T_a = 25^\circ\text{C}$	TO-251 / TO-252	2.5	W
	TO-220	54	
Operating Junction Temperature	T_J	+150	$^\circ\text{C}$
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$



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Thermal Performance

Parameter		Symbol	Limit	Unit
Thermal Resistance - Junction to Case	TO-251 / TO-252	$R_{\theta_{JC}}$	2.87	$^{\circ}\text{C/W}$
	TO-220		2.32	
Thermal Resistance - Junction to Ambient	TO-251 / TO-252	$R_{\theta_{JA}}$	110	$^{\circ}\text{C/W}$
	TO-220		62.5	

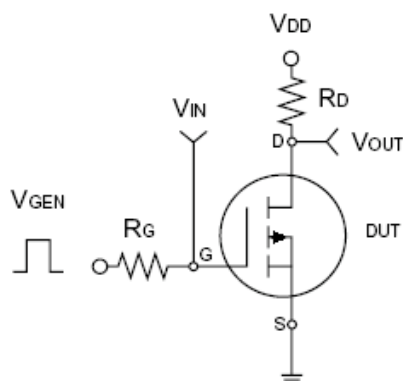
Notes: Surface mounted on FR4 board $t \leq 10\text{sec}$

Electrical Specifications ($T_a = 25^{\circ}\text{C}$ unless otherwise noted)

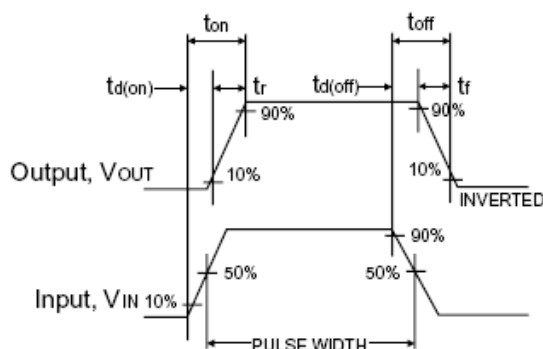
Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV_{DSS}	600	--	--	V
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 1A$	$R_{DS(ON)}$	--	--	4.4	Ω
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	$V_{GS(TH)}$	2.0	--	4.0	V
Zero Gate Voltage Drain Current	$V_{DS} = 600V, V_{GS} = 0V$	I_{DSS}	--	--	10	μA
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I_{GSS}	--	--	± 100	nA
Forward Transconductance	$V_{DS} = 40V, I_D = 1A$	g_{fs}	--	5	--	S
Diode Forward Voltage	$I_S = 2A, V_{GS} = 0V$	V_{SD}	--	--	1.6	V
Dynamic ^b						
Total Gate Charge	$V_{DS} = 400V, I_D = 2A,$ $V_{GS} = 10V$	Q_g	--	13	22	nC
Gate-Source Charge		Q_{gs}	--	2	--	
Gate-Drain Charge		Q_{gd}	--	6	--	
Input Capacitance	$V_{DS} = 25V, V_{GS} = 0V,$ $f = 1.0MHz$	C_{iss}	--	435	--	pF
Output Capacitance		C_{oss}	--	56	--	
Reverse Transfer Capacitance		C_{rss}	--	9.2	--	
Switching ^c						
Turn-On Delay Time	$V_{GS} = 10V, I_D = 2A,$ $V_{DD} = 300V, R_G = 18\Omega$	$t_{d(on)}$	--	12	--	nS
Turn-On Rise Time		t_r	--	21	--	
Turn-Off Delay Time		$t_{d(off)}$	--	30	--	
Turn-Off Fall Time		t_f	--	24	--	

Notes:

- Pulse test: pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$
- For design reference only, not subject to production testing.
- Switching time is essentially independent of operating temperature.



Switching Test Circuit



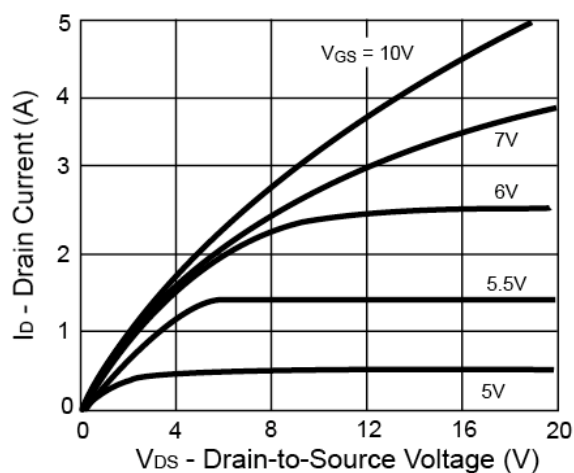
Switchin Waveforms

TSM2N60

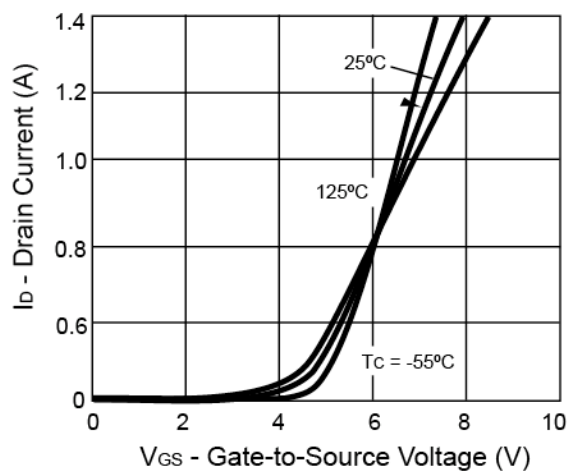
600V N-Channel Power MOSFET

Electrical Characteristics Curve ($T_a = 25^\circ\text{C}$, unless otherwise noted)

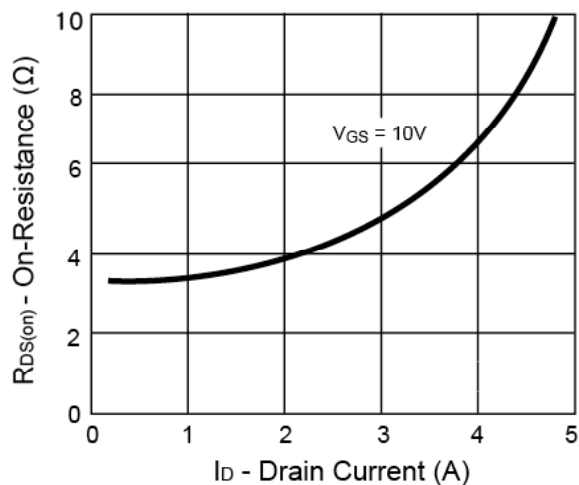
Output Characteristics



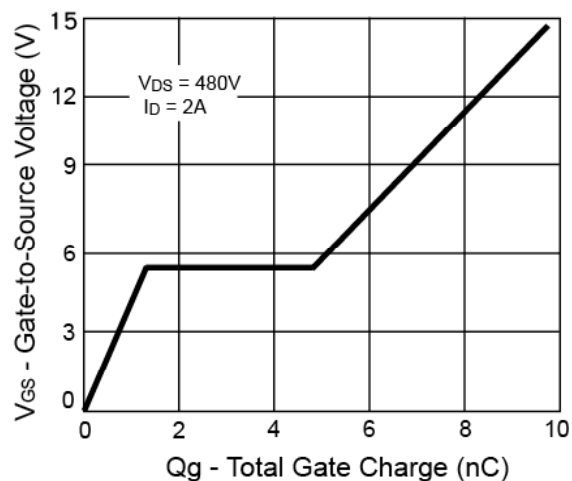
Transfer Characteristics



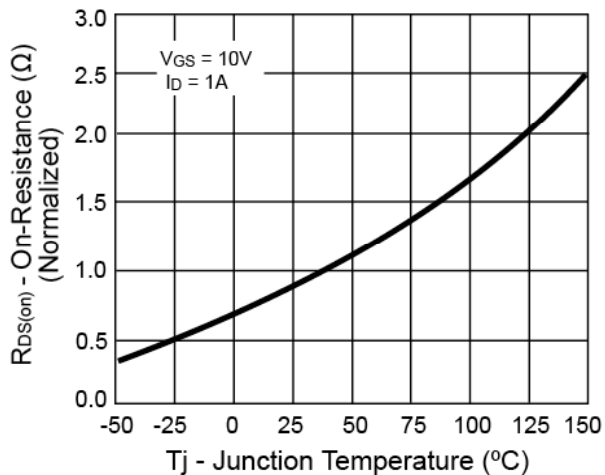
On-Resistance vs. Drain Current



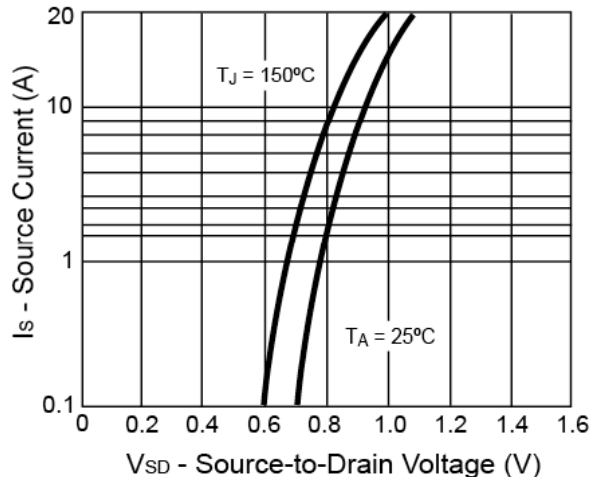
Gate Charge



On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage

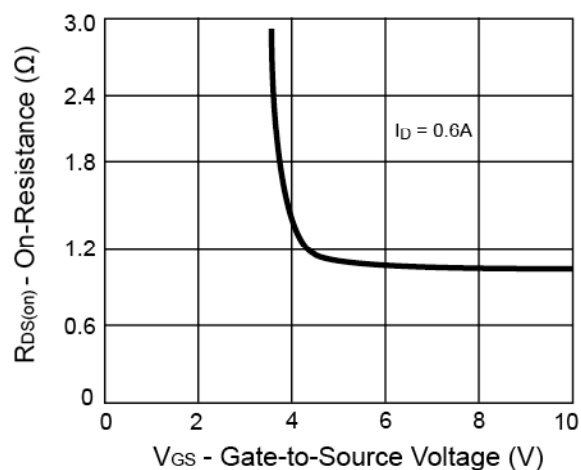


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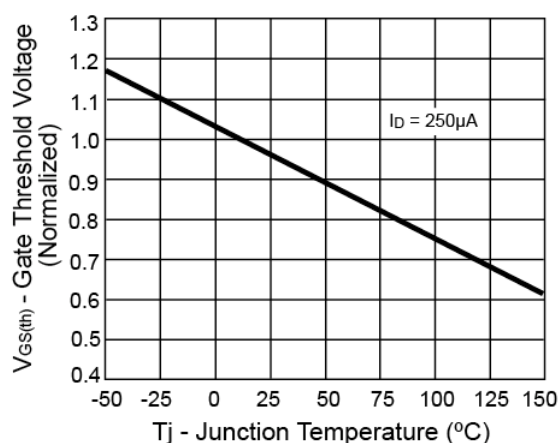
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Electrical Characteristics Curve ($T_a = 25^\circ\text{C}$, unless otherwise noted)

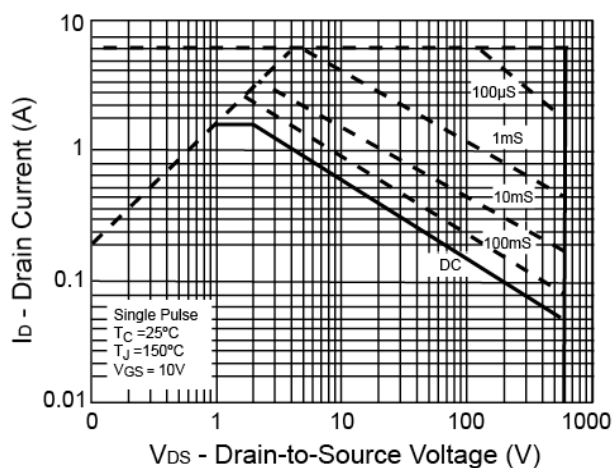
On-Resistance vs. Gate-Source Voltage



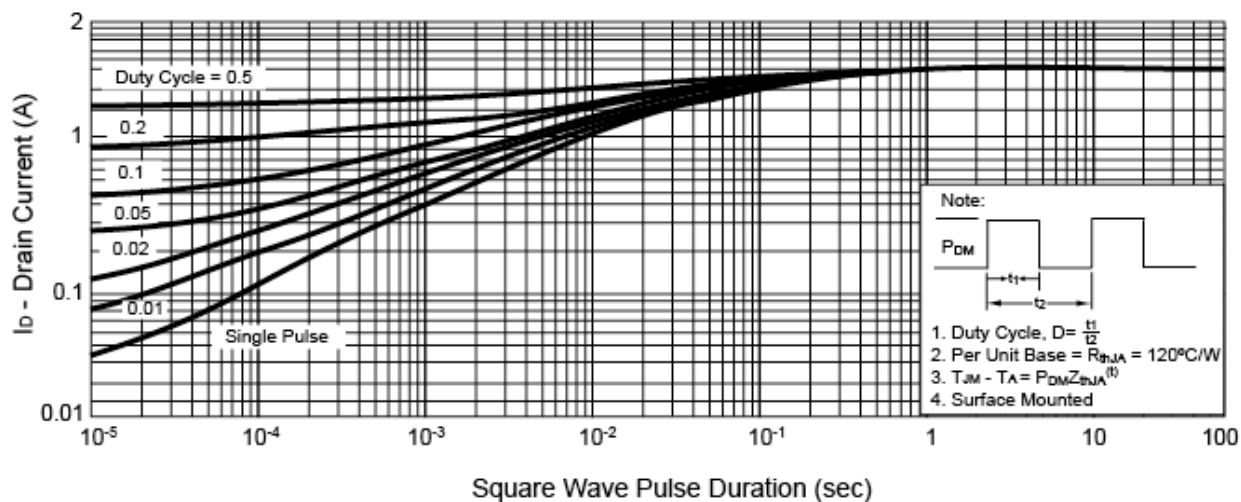
Threshold Voltage



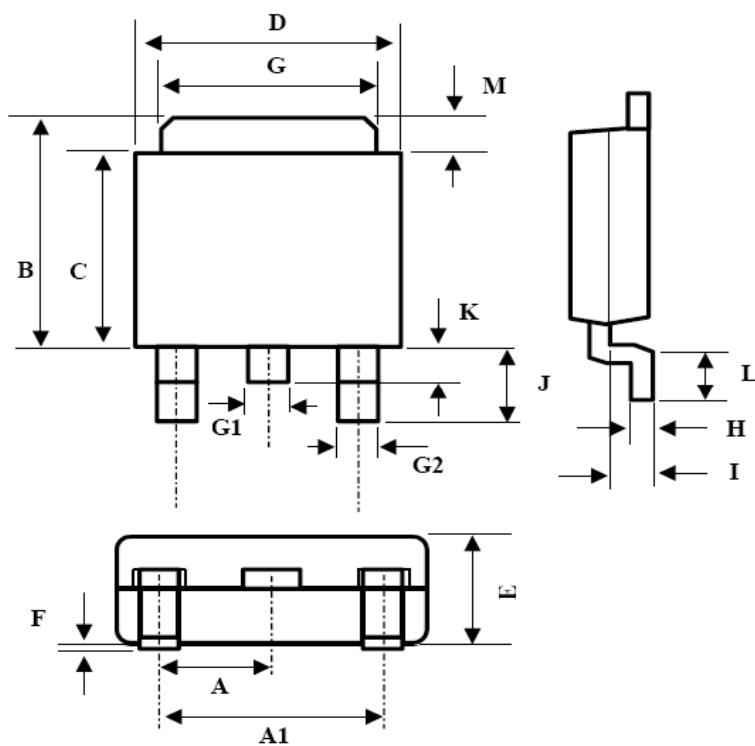
Maximum Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

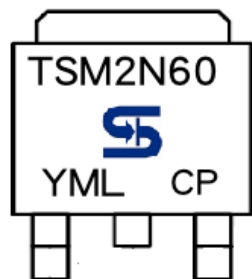


SOT-252 Mechanical Drawing



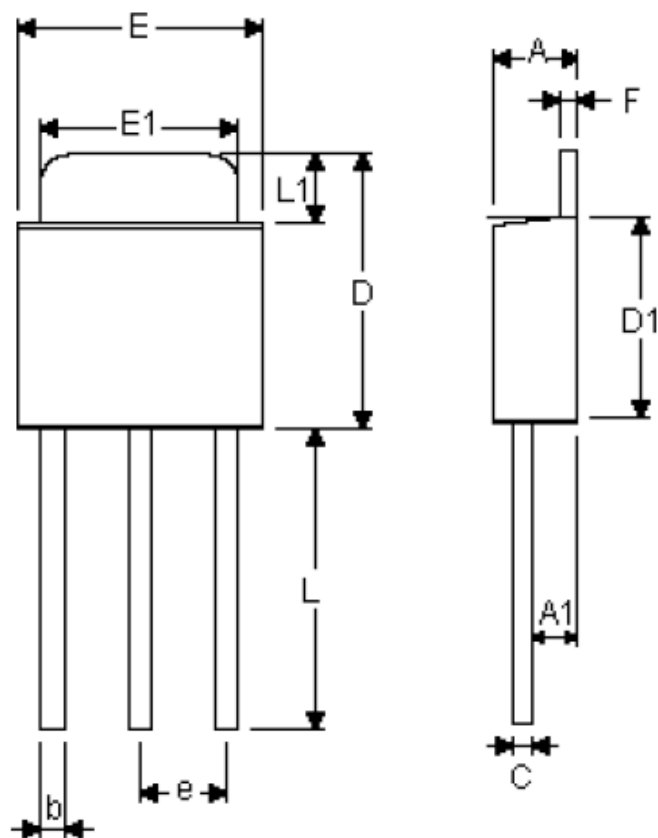
TO-252 DIMENSION				
DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.3BSC		0.09BSC	
A1	4.6BSC		0.18BSC	
B	6.80	7.20	0.268	0.283
C	5.40	5.60	0.213	0.220
D	6.40	6.65	0.252	0.262
E	2.20	2.40	0.087	0.094
F	0.00	0.20	0.000	0.008
G	5.20	5.40	0.205	0.213
G1	0.75	0.85	0.030	0.033
G2	0.55	0.65	0.022	0.026
H	0.35	0.65	0.014	0.026
I	0.90	1.50	0.035	0.059
J	2.20	2.80	0.087	0.110
K	0.50	1.10	0.020	0.043
L	0.90	1.50	0.035	0.059
M	1.30	1.70	0.051	0.67

Marking Diagram



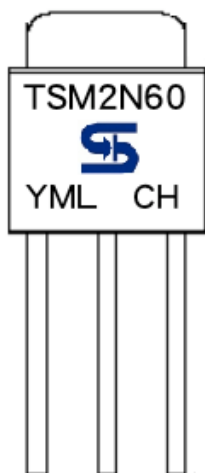
- Y** = Year Code
M = Month Code
 (A=Jan, B=Feb, C=Mar, D=Apr, E=May, F=Jun, G=Jul, H=Aug, I=Sep, J=Oct, K=Nov, L=Dec)
L = Lot Code

SOT-251 Mechanical Drawing



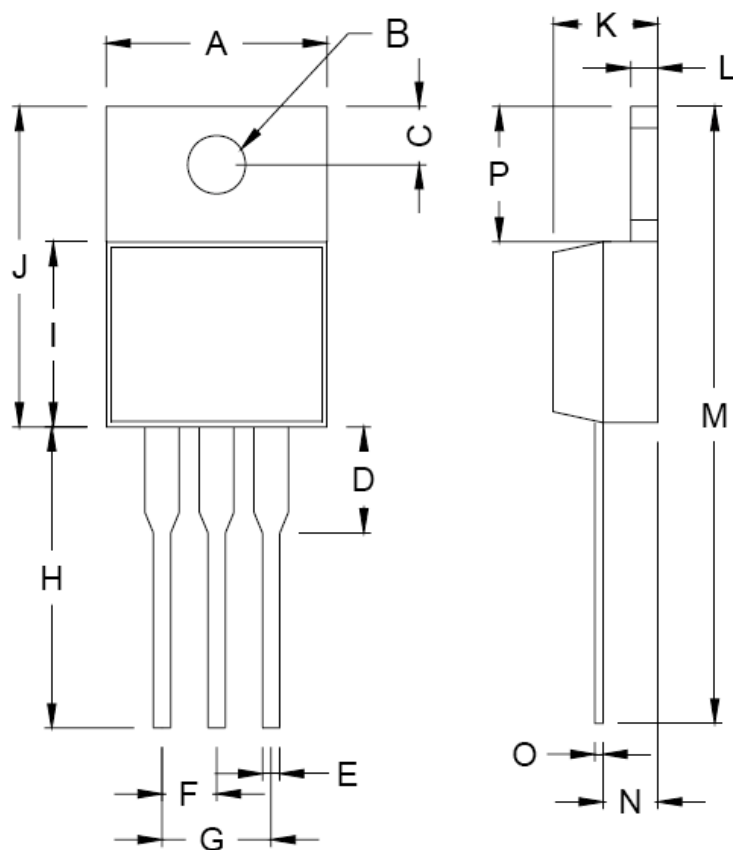
DIM	TO-251 DIMENSION			
	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.20	2.40	0.087	0.094
A1	1.10	1.30	0.043	0.051
b	0.55	0.75	0.022	0.030
C	0.48	0.58	0.019	0.023
D	6.50	7.00	0.256	0.276
D1	5.50	5.70	0.217	0.224
E	6.40	6.60	0.252	0.260
E1	5.20	5.40	0.205	0.213
e	2.25	2.35	0.089	0.093
F	0.48	0.58	0.019	0.023
L	7.80	8.20	0.307	0.323
L1	1.00	1.30	0.039	0.051

Marking Diagram



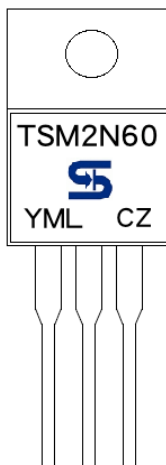
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TO-220 Mechanical Drawing



DIM	TO-220 DIMENSION			
	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	10.000	10.500	0.394	0.413
B	3.740	3.910	0.147	0.154
C	2.440	2.940	0.096	0.116
D	-	6.350	-	0.250
E	0.381	1.106	0.015	0.040
F	2.345	2.715	0.092	0.058
G	4.690	5.430	0.092	0.107
H	12.700	14.732	0.500	0.581
J	14.224	16.510	0.560	0.650
K	3.556	4.826	0.140	0.190
L	0.508	1.397	0.020	0.055
M	27.700	29.620	1.060	1.230
N	2.032	2.921	0.080	0.115
O	0.255	0.610	0.010	0.024
P	5.842	6.858	0.230	0.270

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